74HC2G125-Q100; 74HCT2G125-Q100

Dual buffer/line driver; 3-state

Rev. 1 — 3 April 2013 Product data sheet

1. General description

The 74HC2G125-Q100; 74HC2G125-Q100 are dual buffer/line drivers with 3-state outputs controlled by the output enable inputs ($n\overline{OE}$). Inputs include clamp diodes which enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from −40 °C to +85 °C and from −40 °C to +125 °C
- Input levels:
  - For 74HC2G125-Q100: CMOS level
  - For 74HCT2G125-Q100: TTL level
- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power consumption
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G125DP-Q100	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HCT2G125DP-Q100				
74HC2G125DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HCT2G125DC-Q100				

4. Marking

Table 2. Marking

Type number	Marking code[1]
74HC2G125DP-Q100	H25
74HCT2G125DP-Q100	T25
74HC2G125DC-Q100	H25
74HCT2G125DC-Q100	T25

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

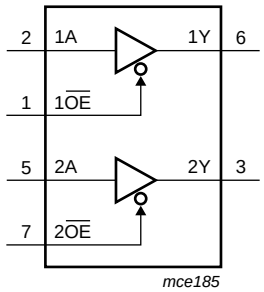


Fig 1. Logic symbol

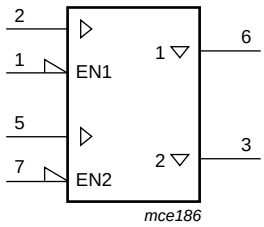


Fig 2. IEC logic symbol

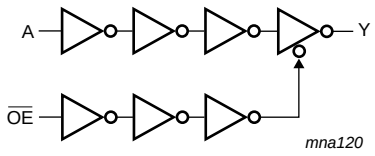


Fig 3. Logic diagram (one driver)

6. Pinning information

6.1 Pinning

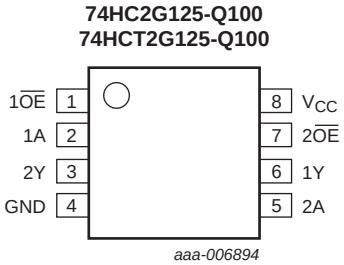


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
$1\overline{OE}$, $2\overline{OE}$	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V_{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Control	Input	Output
$n\overline{OE}$	**nA**	**nY**
L	L	L
L	H	H
H	X	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	-	±20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	[1]	-	35	mA
I_{CC}	supply current			-	70	mA

Table 5. Limiting values *...continued*

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
I_{GND}	ground current			−70	-	mA
T_{stg}	storage temperature			−65	+150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +125 °C	[2]	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC2G125-Q100			74HCT2G125-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	+25	+125	−40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	T_{amb} = −40 °C to +85 °C			T_{amb} = −40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC2G125-Q100								
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	V
		I_O = −6.0 mA; V_{CC} = 4.5 V	3.84	4.32	-	3.7	-	V
		I_O = −7.8 mA; V_{CC} = 6.0 V	5.34	5.81	-	5.2	-	V

Table 7. Static characteristics *...continued*

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C			T_{amb} = –40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±5.0	-	±10	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	10	-	20	μA
C_I	input capacitance		-	1.0	-	-	-	pF
C_O	output capacitance		-	1.5	-	-	-	pF
74HCT2G125-Q100								
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V						
		I_O = –20 μA	4.4	4.5	-	4.4	-	V
		I_O = –6.0 mA	3.84	4.32	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V						
		I_O = 20 μA	-	0	0.1	-	0.1	V
		I_O = 6.0 mA	-	0.16	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; $V_O = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±5.0	-	±10	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; V_{CC} = 4.5 V to 5.5 V; $V_I = V_{CC}$ – 2.1 V; I_O = 0 A	-	-	375	-	410	μA
C_I	input capacitance		-	1.0	-	-	-	pF
C_O	output capacitance		-	1.5	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 7.

Symbol	Parameter	Conditions		T_{amb} = –40 °C to +85 °C			T_{amb} = –40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
74HC2G125-Q100									
t_{pd}	propagation delay	nA to nY; see Figure 5	[2]						
		V_{CC} = 2.0 V		-	35	115	-	135	ns
		V_{CC} = 4.5 V		-	11	23	-	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	10	-	-	-	ns
		V_{CC} = 6.0 V		-	8	20	-	23	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 6	[2]						
		V_{CC} = 2.0 V		-	40	115	-	135	ns
		V_{CC} = 4.5 V		-	11	23	-	27	ns
		V_{CC} = 6.0 V		-	8	20	-	23	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 6	[2]						
		V_{CC} = 2.0 V		-	24	125	-	150	ns
		V_{CC} = 4.5 V		-	12	25	-	30	ns
		V_{CC} = 6.0 V		-	10	21	-	26	ns
t_t	transition time	see Figure 5	[2]						
		V_{CC} = 2.0 V		-	18	75	-	90	ns
		V_{CC} = 4.5 V		-	6	15	-	18	ns
		V_{CC} = 6.0 V		-	5	13	-	15	ns
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC}	[3]						
		output enabled		-	11	-	-	-	pF
		output disabled		-	1	-	-	-	pF
74HCT2G125-Q100									
t_{pd}	propagation delay	nA to nY; see Figure 5	[2]						
		V_{CC} = 4.5 V		-	15	31	-	38	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	12	-	-	-	ns
t_{en}	enable time	$n\overline{OE}$ to nY; see Figure 6; V_{CC} = 4.5 V	[2]	-	15	35	-	42	ns
t_{dis}	disable time	$n\overline{OE}$ to nY; see Figure 6; V_{CC} = 4.5 V	[2]	-	15	31	-	38	ns
t_t	transition time	see Figure 5; V_{CC} = 4.5 V	[2]	-	6	15	-	18	ns

Table 8. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 7.

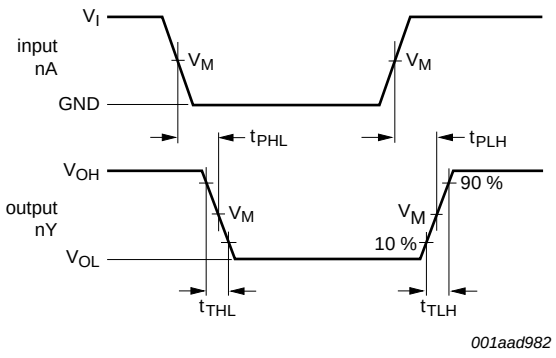
Symbol	Parameter	Conditions	T_{amb} = –40 °C to +85 °C			T_{amb} = –40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC} − 1.5 V [3]						
		output enabled	-	11	-	-	-	pF
		output disabled	-	1	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZL} and t_{PZH}.
t_{dis} is the same as t_{PLZ} and t_{PHZ}.
t_t is the same as t_{THL} and t_{TLH}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

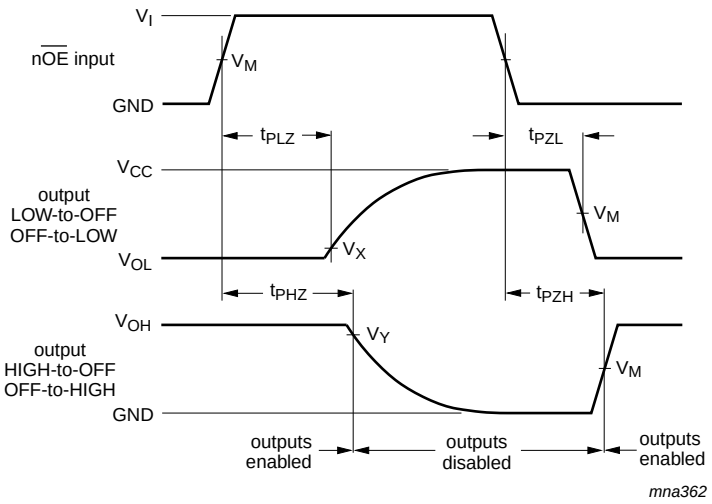
12. Waveforms



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Propagation delays data input (nA) to output (nY)



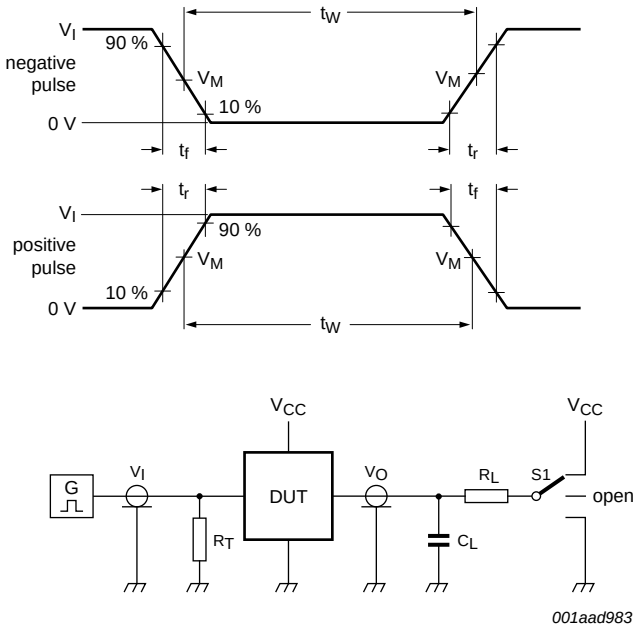
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. Enable and disable times

Table 9. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC2G125-Q100	$0.5V_{CC}$	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V
74HCT2G125-Q100	1.3 V	1.3 V	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 10.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

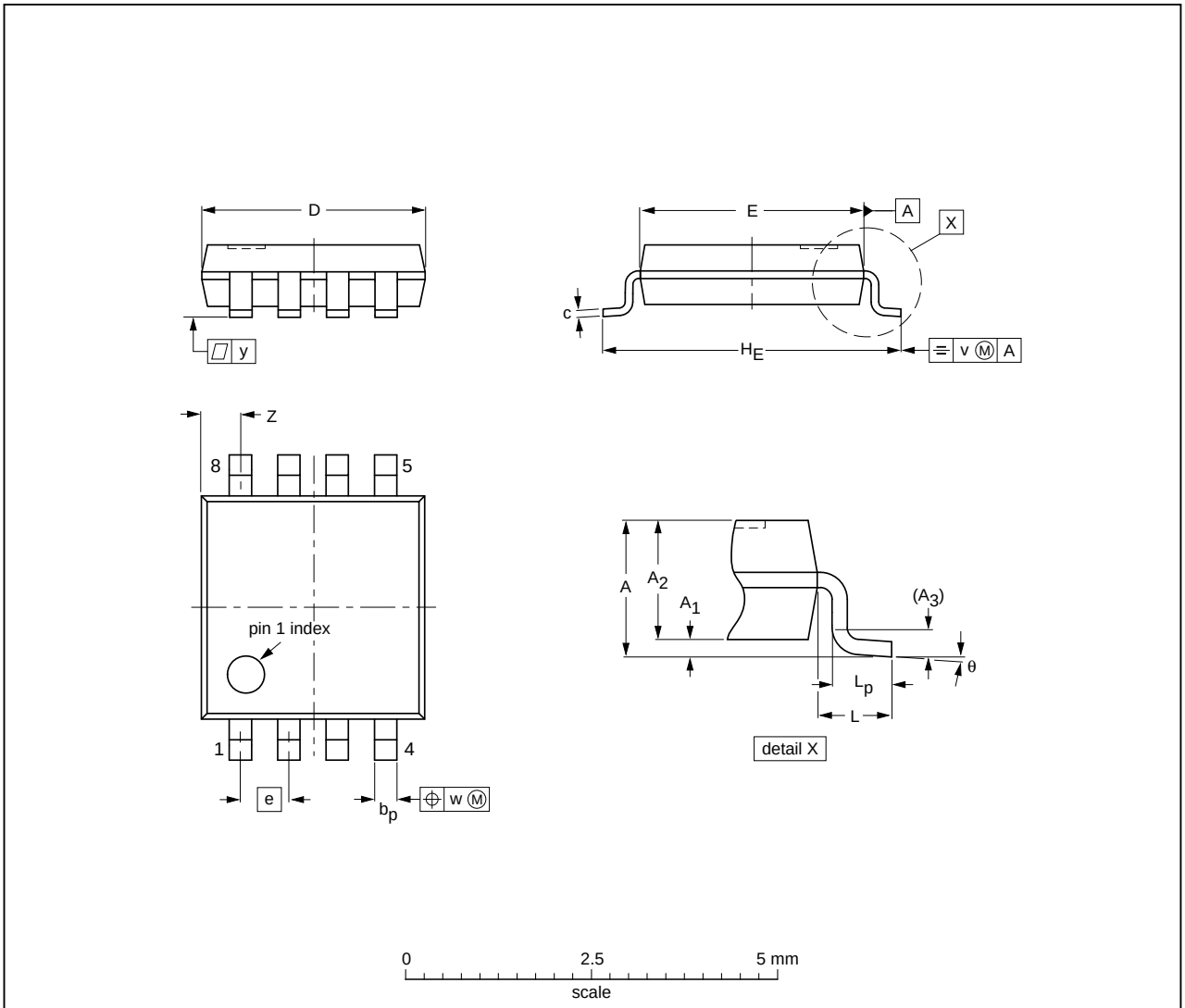
Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC2G125-Q100	V_{CC}	≤ 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}
74HCT2G125-Q100	3 V	≤ 6 ns	15 pF, 50 pF	1 kΩ	open	GND	V_{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	v	w	y	$Z^{(1)}$	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

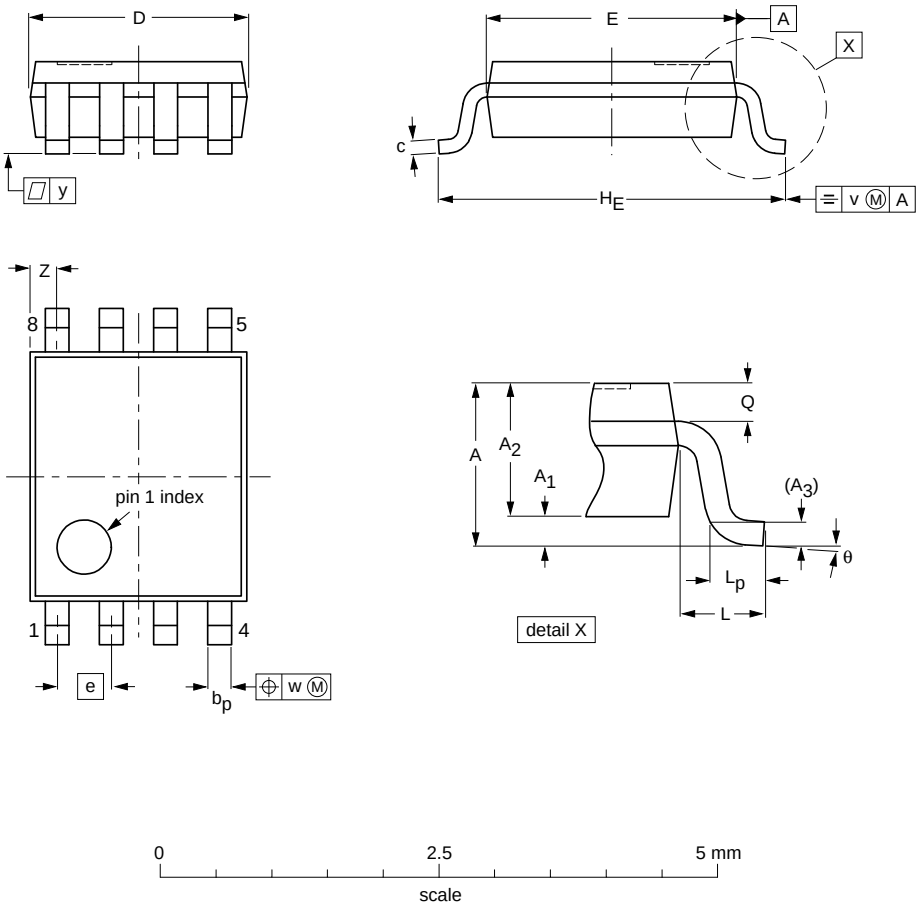
Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 9. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G125_Q100 v.1	20130403	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: **http://www.nxp.com**

For sales office addresses, please send an email to: **salesaddresses@nxp.com**

18. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 3 April 2013
Document identifier: 74HC_HCT2G125_Q100

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Logic Gates ***category:***

Click to view products by NXP ***manufacturer:***

Other Similar products are found below :

5962-8769901BCA 74HC85N NL17SG08P5T5G NL17SG32DFT2G NLU1G32AMUTCG NLV7SZ58DFT2G NLVHC1G08DFT1G NLVVHC1G14DTT1G NLX2G08DMUTCG NLX2G08MUTCG MC74HCT20ADR2G 091992B 091993X 093560G 634701C 634921A NL17SG32P5T5G NL17SG86DFT2G NLV14001UBDR2G NLVVHC1G132DTT1G NLVVHC1G86DTT1G NLX1G11AMUTCG NLX1G97MUTCG 746427X 74AUP1G17FW5-7 74LS38 74LVC1G08Z-7 74LVC32ADTR2G 74LVC1G125FW4-7 74LVC08ADTR2G MC74HCT20ADTR2G NLV14093BDTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G NLV17SZ126DFT2G NLV27WZ17DFT2G NLV74HC02ADR2G NLV74HC08ADR2G NLVVHC1GT32DFT1G 74HC32S14-13 74LS133 74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7 M38510/06202BFA NLV74HC08ADTR2G NLV74HC14ADR2G NLV74HC20ADR2G NLV74VHC1G08DTT1G